

2SD768(K)

Silicon NPN Epitaxial

HITACHI

Application

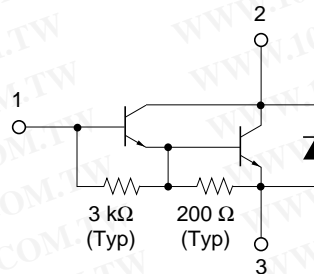
Medium speed and power switching complementary pair with 2SB727(K)

Outline

TO-220AB



1. Base
2. Collector (Flange)
3. Emitter



勝特力材料 886-3-5753170
勝特力电子(上海) 86-21-54151736
勝特力电子(深圳) 86-755-83298787
[Http://www.100y.com.tw](http://www.100y.com.tw)

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	120	V
Collector to emitter voltage	V_{CEO}	120	V
Emitter to base voltage	V_{EBO}	7	V
Collector current	I_C	6	A
Collector peak current	$I_{C(peak)}$	10	A
Collector power dissipation	P_C^{*1}	40	W
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

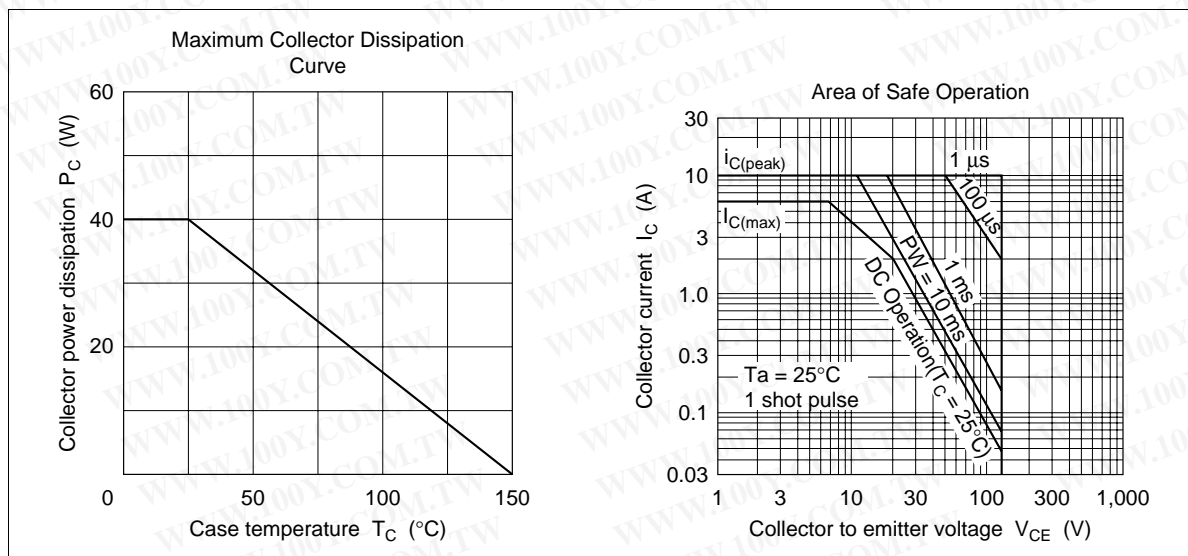
Note: 1. Value at $T_c = 25^\circ\text{C}$.

2SD768(K)

Electrical Characteristics (Ta = 25°C)

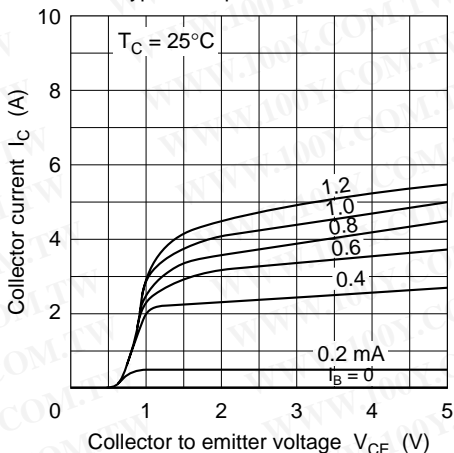
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	120	—	—	V	$I_C = 25 \text{ mA}$, $R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	7	—	—	V	$I_E = 50 \text{ mA}$, $I_C = 0$
Collector cutoff current	I_{CBO}	—	—	100	μA	$V_{CB} = 120 \text{ V}$, $I_E = 0$
	I_{CEO}	—	—	10	μA	$V_{CE} = 100 \text{ V}$, $R_{BE} = \infty$
DC current transfer ratio	h_{FE}	1000	—	20000		$V_{CE} = 3 \text{ V}$, $I_C = 3 \text{ A}^{*1}$
Collector to emitter saturation voltage	$V_{CE(sat)1}$	—	—	1.5	V	$I_C = 3 \text{ A}$, $I_B = 6 \text{ mA}^{*1}$
	$V_{CE(sat)2}$	—	—	3	V	$I_C = 6 \text{ A}$, $I_B = 60 \text{ mA}^{*1}$
Base to emitter saturation voltage	$V_{BE(sat)1}$	—	—	2	V	$I_C = 3 \text{ A}$, $I_B = 6 \text{ mA}^{*1}$
	$V_{BE(sat)2}$	—	—	3.5	V	$I_C = 6 \text{ A}$, $I_B = 60 \text{ mA}^{*1}$
Turn on time	t_{on}	—	1.0	—	μs	$I_C = 3 \text{ A}$, $I_{B1} = -I_{B2} = 6 \text{ mA}$
Turn off time	t_{off}	—	3.0	—	μs	$I_C = 3 \text{ A}$, $I_{B1} = -I_{B2} = 6 \text{ mA}$

Note: 1. Pulse test.

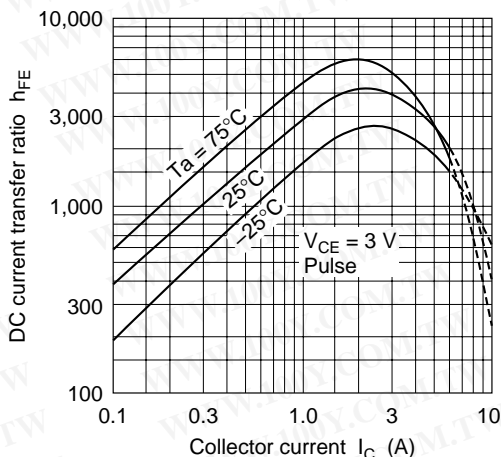


勝特力材料 886-3-5753170
 勝特力电子(上海) 86-21-54151736
 勝特力电子(深圳) 86-755-83298787
[Http://www.100y.com.tw](http://www.100y.com.tw)

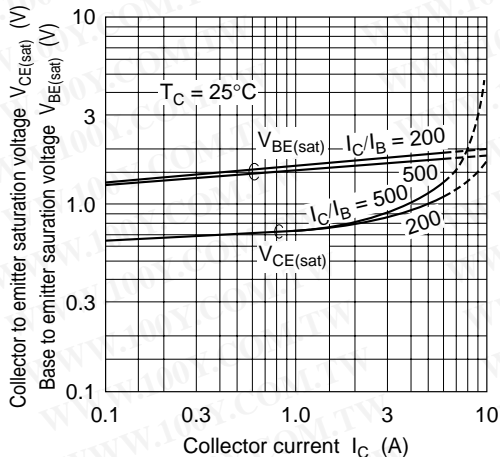
Typical Output Characteristics



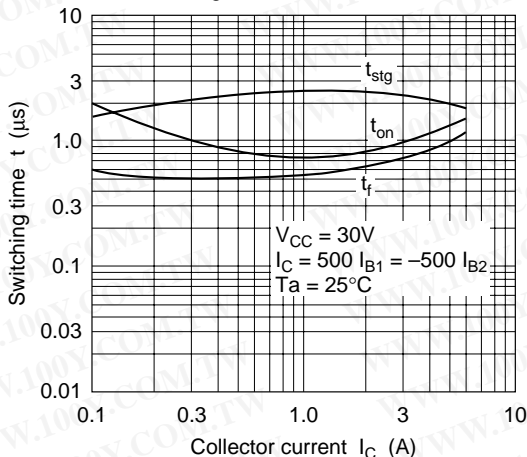
DC Current Transfer Ratio vs. Collector Current



Saturation Voltage vs. Collector Current

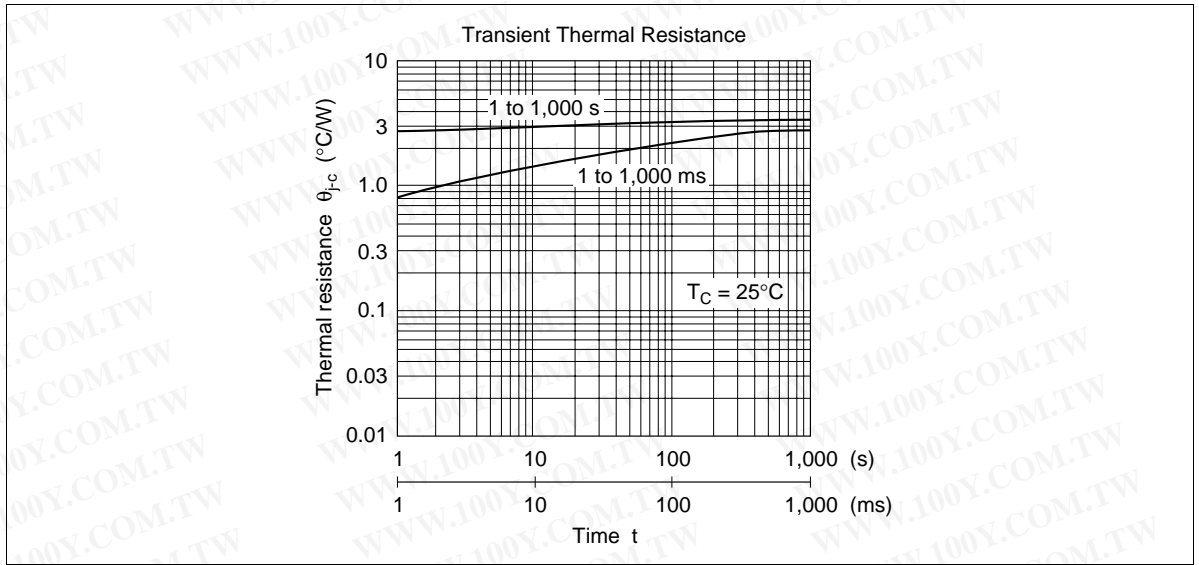


Switching Time vs. Collector Current



勝特力材料 886-3-5753170
 勝特力电子(上海) 86-21-54151736
 勝特力电子(深圳) 86-755-83298787
[Http://www.100y.com.tw](http://www.100y.com.tw)

2SD768(K)



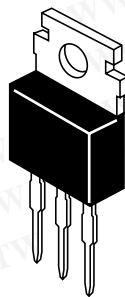
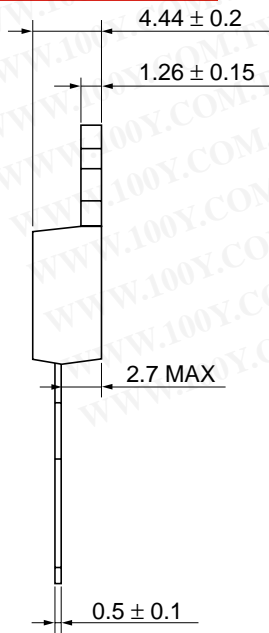
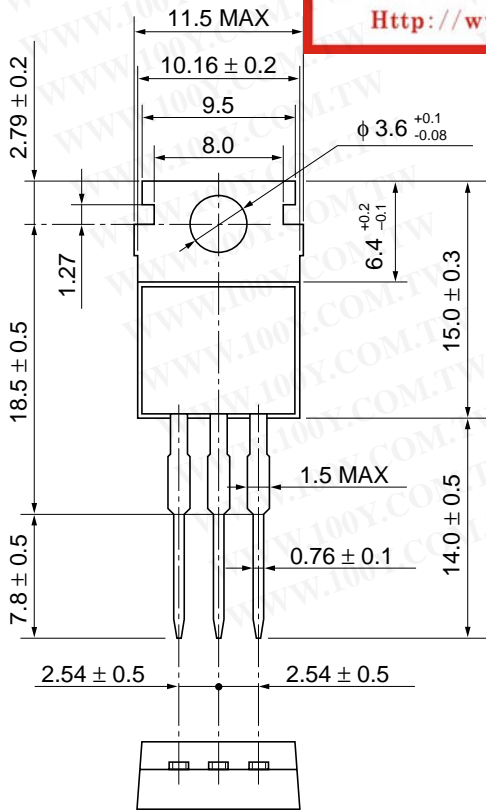
勝特力材料 886-3-5753170
勝特力电子(上海) 86-21-54151736
勝特力电子(深圳) 86-755-83298787
[Http://www.100y.com.tw](http://www.100y.com.tw)

勝特力材料 886-3-5753170

勝特力电子(上海) 86-21-54151736

勝特力电子(深圳) 86-755-83298787

[Http://www.100y.com.tw](http://www.100y.com.tw)



Hitachi Code	TO-220AB
JEDEC	Conforms
EIAJ	Conforms
Weight (reference value)	1.8 g

勝特力材料 886-3-5753170
勝特力电子(上海) 86-21-54151736
勝特力电子(深圳) 86-755-83298787
[Http://www.100y.com.tw](http://www.100y.com.tw)

Cautions

1. Hitachi neither warrants nor grants licenses of any rights of Hitachi's or any third party's patent, copyright, trademark, or other intellectual property rights for information contained in this document. Hitachi bears no responsibility for problems that may arise with third party's rights, including intellectual property rights, in connection with use of the information contained in this document.
2. Products and product specifications may be subject to change without notice. Confirm that you have received the latest product standards or specifications before final design, purchase or use.
3. Hitachi makes every attempt to ensure that its products are of high quality and reliability. However, contact Hitachi's sales office before using the product in an application that demands especially high quality and reliability or where its failure or malfunction may directly threaten human life or cause risk of bodily injury, such as aerospace, aeronautics, nuclear power, combustion control, transportation, traffic, safety equipment or medical equipment for life support.
4. Design your application so that the product is used within the ranges guaranteed by Hitachi particularly for maximum rating, operating supply voltage range, heat radiation characteristics, installation conditions and other characteristics. Hitachi bears no responsibility for failure or damage when used beyond the guaranteed ranges. Even within the guaranteed ranges, consider normally foreseeable failure rates or failure modes in semiconductor devices and employ systemic measures such as fail-safes, so that the equipment incorporating Hitachi product does not cause bodily injury, fire or other consequential damage due to operation of the Hitachi product.
5. This product is not designed to be radiation resistant.
6. No one is permitted to reproduce or duplicate, in any form, the whole or part of this document without written approval from Hitachi.
7. Contact Hitachi's sales office for any questions regarding this document or Hitachi semiconductor products.

HITACHI

HITACHI